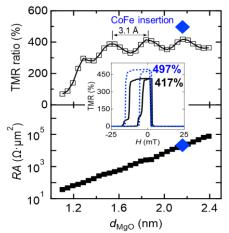
## Single-crystal Fe/MgO/Fe magnetic tunnel junctions with a room temperature magnetoresistance of 417% NIMS, °T. Scheike, Xiang, Z. Wen, H. Sukegawa, T. Ohkubo, K. Hono, S. Mitani E-mail: scheike.thomas@nims.go.jp

Magnetic tunnel junctions (MTJs) are important building blocks for novel spintronics applications, e.g., brain-morphic devices and magnetic logic circuits, which are in need of very large tunnel magnetoresistance (TMR) ratios possibly exceeding 1000% at room temperature (RT) for their operation [1]. Therefore, significant enhancement in experimental TMR is needed. Even in a simple Fe/MgO/Fe MTJ, there is large discrepancy between experiments (~180%) [2] and theories that predict TMR >1000%. To bridge the discrepancy, we revisited the Fe/MgO/Fe MTJ by all layer optimization for production; as a result, we achieved a TMR ratio up to 417% at RT, almost doubling previous reports of Fe/MgO/Fe [3].

MTJs were deposited using an ultrahigh vacuum magnetron sputtering with a structure of MgO(001) substrate//Cr (60)/Fe (50)[/CoFe (2.24)]/Mg (0.5)/wedge-shaped MgO ( $d_{MgO}$ )/natural oxidation/Fe (5)/IrMn (10)/Ru (20) (in nm). All layer processes were tuned to improve the crystal quality of the top- and bottom-Fe/MgO interfaces. Wafers were *ex-situ* annealed in a 0.7 T magnetic field at 200°C and patterned into micrometer scale MTJs. The transport properties were investigated using a DC 4-probe method.

In Fig. 1, the RT TMR ratio and *RA* vs.  $d_{MgO}$  for the Fe/MgO/Fe MTJ after optimization is shown. The maximum TMR ratio reaches 417% at RT (see the MR loop in the inset). The TMR ratio shows oscillations with  $d_{MgO}$  and a period of 3.1 Å, similar to the previous Fe/MgO/Fe report [2]. Surprisingly, the maximum peak-to-valley difference is ~80%, which is 7 times larger than that of the reported values [2]. The obtained TMR ratio is almost twice as large as previously reported values of Fe/MgO/Fe, demonstrating that there is more room for larger TMR ratios in typical MTJs by using material optimization and interface tuning. In fact, we obtain a much larger TMR ratio of



**Fig. 1** TMR and *RA* vs.  $d_{MgO}$ ; inset: maximum TMR loop of Fe/MgO/Fe and Fe/CoFe/MgO/Fe MTJ.

497% using a CoFe insertion, i.e., Fe/CoFe (2.24)/MgO/Fe, as shown as the diamond of Fig. 1.

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**Reference:** [1] Y. Cao *et al.*, iScience **23**, 101614 (2020); [2] S. Yuasa *et al.*, Nat. Mater. **3**, 868 (2004); [3] T. Scheike *et al.*, Appl. Phys Lett., in-press; arXiv: 2011.08739.